International Rectifier

10BQ060PbF

SCHOTTKY RECTIFIER

1 Amp

 $I_{F(AV)} = 1.0 Amp$ $V_R = 60 V$

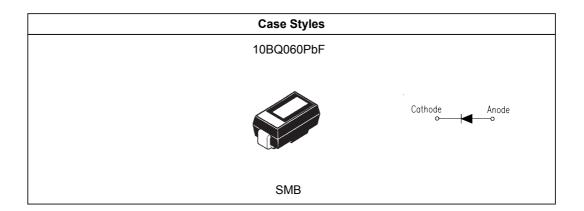
Major Ratings and Characteristics

Characteristics	10BQ060	Units				
I _{F(AV)} Rectangular waveform	1.0	Α				
V _{RRM}	60	V				
I _{FSM} @tp=5 µs sine	700	А				
V _F @1.0 Apk, T _J =125°C	0.57	V				
T _J range	-55 to 150	°C				

Description/ Features

The 10BQ060 surface-mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging, and reverse battery protection.

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Lead-Free ("PbF" suffix)



Bulletin PD-20785 07/04

International Rectifier

Voltage Ratings

Part number	10BQ060PbF
V _R Max. DC Reverse Voltage (V)	00
V _{RWM} Max. Working Peak Reverse Voltage (V)	60

Absolute Maximum Ratings

	Parameters	10BQ	Units	Conditions	
I _{F(AV)}	Max. Average Forward Current	1.0	Α	50% duty cycle @ T _L = 103 °C, rectangular wave form	
I _{FSM}	Max. Peak One Cycle Non-Repetitive	700	Α	5μs Sine or 3μs Rect. pulse	Following any rated load condition and
	Surge Current	42		10ms Sine or 6ms Rect. pulse	with rated V _{RRM} applied
E _{AS}	Non-Repetitive Avalanche Energy	2.0	mJ	T _J =25 °C, I _{AS} = 1A, L = 4mH	
I _{AR}	Repetitive Avalanche Current	1.0	А	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max. Va = 1.5 x Vr typical	

Electrical Specifications

	Parameters	10BQ	Units		Conditions
V _{FM}	Max. Forward Voltage Drop (1)	0.6	V	@ 1A	T = 25 °C
	* See Fig. 1	0.76	V	@ 2A	T _J = 25 °C
		0.57	V	@ 1A	T _. = 125 °C
		0.69	V	@ 2A	1, 120 0
I _{RM}	Max. Reverse Leakage Current (1)	0.1	mA	T _J = 25 °C	V _P = rated V _P
	* See Fig. 2	5.0	mA	T _J = 125 °C	V _R – rated V _R
C _T	Typical Junction Capacitance	62	pF	V _R = 5V _{DC} (test signal range 100kHz to 1MHz) 25°C	
L _s	Typical Series Inductance	2.0	nH	Measured lead to lead 5mm from package body	
dv/dt	Max. Volatge Rate of Charge	10000	V/ µs		
	(Rated V _R)				

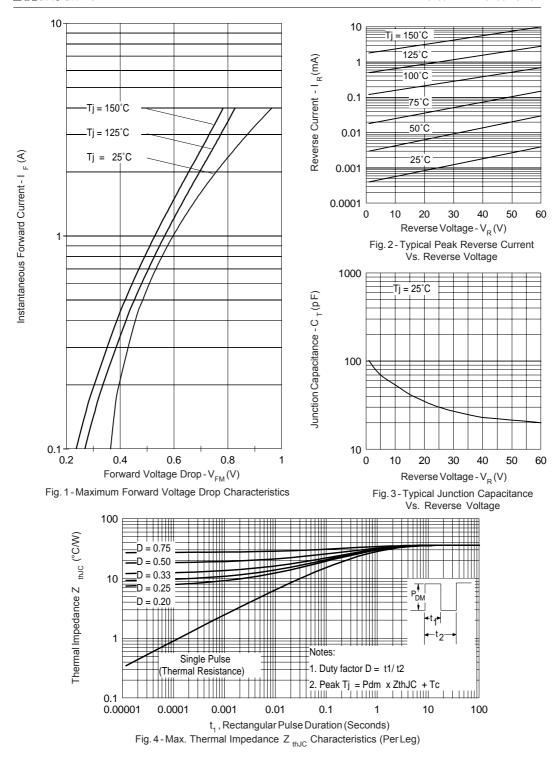
⁽¹⁾ Pulse Width < 300 μ s, Duty Cycle < 2%

Thermal-Mechanical Specifications

	Parameters	10BQ	Units	Conditions
TJ	Max. Junction Temperature Range (*)	-55 to 150	°C	
T _{stg}	Max. Storage Temperature Range	-55 to 150	°C	
R _{thJL}	Max. Thermal Resistance Junction to Lead (**)	36	°C/W	DC operation
R _{thJA}	Max. Thermal Resistance Junction to Ambient	80	°C/W	
wt	Approximate Weight	0.10 (0.003)	g (oz.)	
	Case Style	SMB		Similar DO-214AA
	Device Marking	IR1H		

 $[\]frac{\text{dPtot}}{\text{dTj}} < \frac{1}{\text{Rth(j-a)}} \text{ thermal runaway condition for a diode on its own heatsink}$

^(**) Mounted 1 inch square PCB



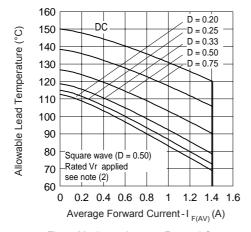


Fig. 4 - Maximum Average Forward Current Vs. Allowable Lead Temperature

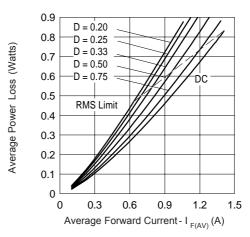


Fig. 5 - Maximum Average Forward Dissipation Vs. Average Forward Current

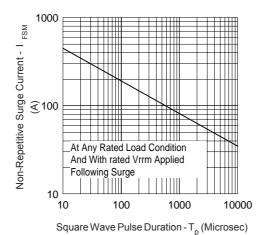
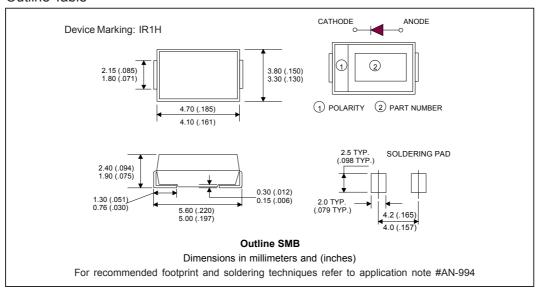


Fig. 6-Maximum Peak Surge Forward Current Vs. Pulse Duration

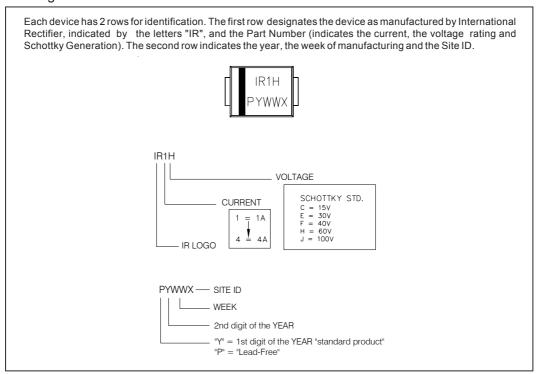
 $\begin{aligned} \textbf{(2)} \ \ &\text{Formula used:} \ &\text{$T_C = T_J - (Pd + Pd_{REV})$} \times R_{thJC}; \\ &\text{$Pd = $Forward Power Loss = I_{F(AV)}$} \times V_{FM} @ (I_{F(AV)} / D) \ \ (\text{see Fig. 6}); \\ &Pd_{REV} = &\text{Inverse Power Loss = V_{R1}} \times I_R (1 - D); \ &I_R @ V_{R1} = 80\% \ \text{rated } V_R \end{aligned}$

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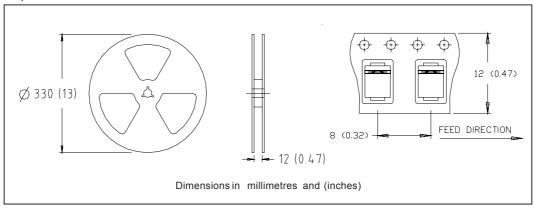
Outline Table



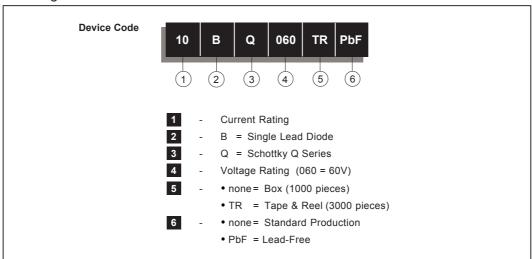
Marking & Identification



Tape & Reel Information



Ordering Information Table



Data and specifications subject to change without notice. This product has been designed and qualified for Industrial Level and Lead-Free.

Qualification Standards can be found on IR's Web site.



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